

TF1388M

3-Phase Half-Bridge Gate Driver

Features

- Three floating high-side drivers in bootstrap operation to 250V
- 420mA source / 750mA sink output current capability
- Logic input 3.3V capability
- Internal deadtime of 315ns to protect MOSFETs
- Matched prop delay time maximum of 50ns
- Outputs in phase with inputs
- Schmitt triggered logic inputs
- Cross conduction prevention logic
- Undervoltage lockout for all channels
- Extended temperature range: -40°C to +125°C
- Space saving SOIC-20 package

Applications

- 3-Phase Motor Inverter Driver
- White Goods Air Conditioner, Washing Machine, Refrigerator
- Industrial Motor Inverter Power Tools, Robotics
- General Purpose 3-Phase Inverter

Description

The TF1388M is a three-phase gate driver IC designed for high voltage three-phase applications, driving N-channel MOSFETs and IGBTs in a half-bridge configuration. TF Semiconductor's high voltage process enables the TF1388M high sides to switch to 250V in a bootstrap operation.

The TF1388M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices and are enabled low to better function in high noise environments. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction.

The TF1388M offers numerous protection functions. A shoot-through protection logic prevents both outputs being high with both inputs high (fault state), an undervoltage lockout for V_{cc} shuts down all drivers through an internal fault control, and a UVLO for V_{BS} shuts down the respective high side output. The TF1388M is offered in SOIC 20 package and operates over an extended -40 °C to +125 °C temperature range.

SOIC-20



Ordering Information

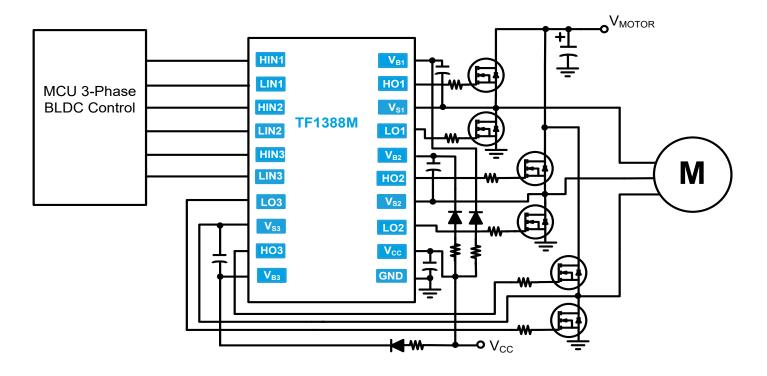
Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF1388M-TGU	SOIC-20	Tube / 35	YYWW
TF1388M-TGH	SOIC-20	T&R / 1500	TF2388M Lot ID

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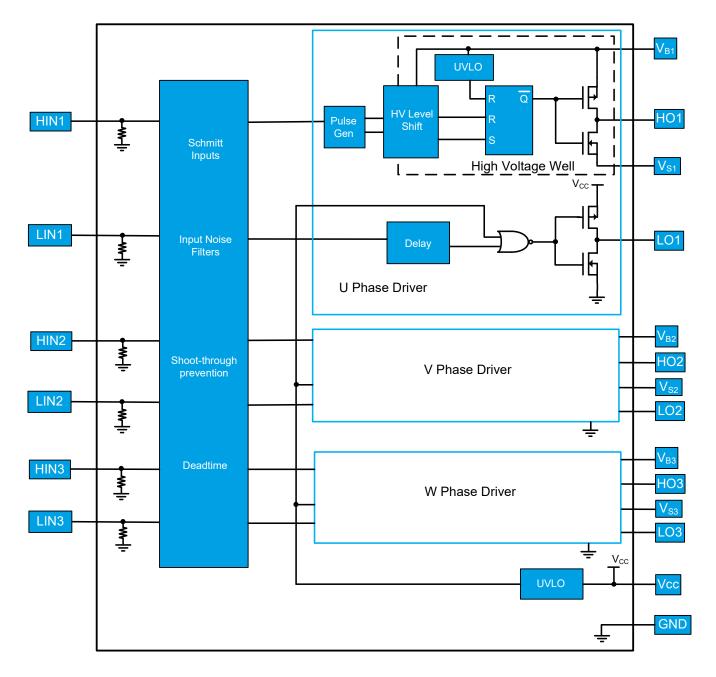


Typical Application





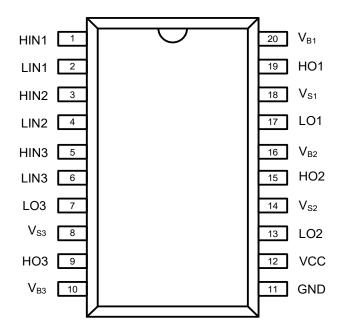
Functional Block Diagram







3-Phase Half-Bridge Gate Driver



Top View: SOIC-20

Pin Descriptions

PIN NAME	PIN NUMBER	PIN DESCRIPTION
HIN1, HIN2, HIN3	1, 3, 5	Logic input for high-side gate driver output, in phase with HO.
LIN1, LIN2, LIN3	2, 4, 6	Logic input for low-side gate driver output, in phase with LO.
LO3, LO2, LO1	7, 13, 17	Low-side gate driver output
V ₅₃ ,V ₅₂ ,V ₅₁	8, 14, 18	High-side floating supply return
HO3, HO2, HO1	9, 15, 19	High-side gate driver output
V _{B3} ,V _{B2} ,V _{B1}	10, 16, 20	High-side floating supply
GND	11	Low-side driver and logic return
VCC	12	Low-side and logic fixed supply



Absolute Maximum Ratings (NOTE1)

V _B - High-side floating supply voltage	0.3V to +274V
V _s - High-side floating supply offset voltage	V_{B} -24V to V_{B} +0.3V
V _{HO} -High-sidefloating output voltage	V _s -0.3VtoV _B +0.3V
V ₁₀ - Low-side output voltage	0.3VtoV _{cc} +0.3V
dV _s /dt-Offset supply voltage transient	50 V/ns
V _{cc} -Low-side fixed supply voltage	0.3V to +24V
V _{IN} -Logic input voltage(HINandLIN)	

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

$P_{\rm D}$ - Package power dissipation at $T_{\rm A}{=}25^{\circ}{\rm C}$ SOIC-201.88W
SOIC-20 Thermal Resistance (N0TE2) θ _{JA}
T _J - Junction operating temperature+150 °C T _L - Lead Temperature (soldering, 10 seconds)+300 °C T _{stg} - Storage temerature55 to 150 °C

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Symbol	Parameter	MIN	МАХ	Unit
V _B	High side floating supply absolute voltage	V _s + 10	V _s + 20	V
Vs	High side floating supply offset voltage	NOTE3	250	V
V _{HO}	High side floating output voltage	Vs	V _B	V
V _{cc}	Low side fixed supply voltage	10	20	V
V _{LO}	Low side output voltage	СОМ	V _{cc}	V
V _{IN}	Logic input voltage (HIN and LIN)	0	5	V
T _A	Ambient temperature	-40	125	°C

NOTE3 Logic operational for VS of -5V to +250V.

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DC Electrical Characteristics (NOTE4)

 $V_{\text{BIAS}}(V_{\text{CC}},V_{\text{BS}}) = 15V, T_{\text{A}} = 25\ ^{\circ}\text{C}$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	ТҮР	МАХ	Unit
V _{IH}	Logic "0" input voltage		2.4			
V _{IL}	Logic "1" input voltage	NOTE5			0.8	
V _{OH}	High level output voltage, V _{BIAS} - V _O	$I_0 = 2mA$		0.2	0.5	
V _{OL}	Low level output voltage, V _o	$I_0 = 2mA$		0.07	0.2	V
I _{LK}	Offset supply leakage current	VB = VS = 250V			10	
I _{BSQ}	Quiescent V _{BS} supply current	$V_{IN} = 0V \text{ or } 5V$		50	80	
I _{BSO}	Operating V _{BS} supply current	fs = 20khz		400		
I _{ccq}	Quiescent V _{cc} supply current	$V_{IN} = 0V \text{ or } 5V$		230	330	μΑ
I _{cco}	Operating V _{cc} supply current	fs = 20khz		500		
I _{IN+}	Logic "1" input bias current	$V_{IN} = 5V$		25	80	
I _{IN-}	Logic "0" input bias current	$V_{IN} = 0V$			2	
R _{IN}	Input pull-down resistance			200		kΩ
V _{BSUV+} V _{CCUV+}	$V_{\scriptscriptstyle BS}$ and $V_{\scriptscriptstyle CC}$ supply under-voltage positive going threshold		7.1	8.5	9.9	
V _{bsuv-} V _{ccuv-}	V _{BS} and V _{CC} supply under-voltage negative going threshold		6.7	8.1	9.5	V
I _{O+}	Output high short circuit pulsed current	$V_{o} = 0V, PW \le 10 \ \mu s$	270	420		
I _{o-}	Output low short circuit pulsed current	$V_{o} = 15V$, PW $\leq 10 \ \mu s$	600	750		mA

NOTE4 The V_{IIV} V_{TIV} and I_{IN} parameters are referenced to V_{ss} and are applicable to all six channels (HIN1,2,3 and LIN1,2,3). The V_o and I_o parameters are applicable to the outputs (HO1,2,3 and LO1,2,3 and

NOTES For optimal operation, it is recommended that the input pulse (to HINx and LINx) should have an amplitude of 2.4V minimum with a pulse width of 600ns minimum.

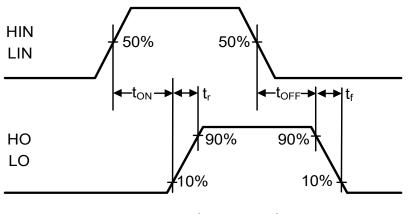


AC Electrical Characteristics

 $V_{_{BIAS}}(V_{_{CC}},V_{_{BS}})$ = 15V, $C_{_L}$ = 1000pF, and $T_{_A}$ = 25 °C , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	ТҮР	МАХ	Unit
t _{on}	Turn-on propogation delay	$V_s = 0V$	70	120	170	
t _{off}	Turn-off propogation delay	$V_s = 0V$	70	120	170	ns
t _r	Turn-on rise time			45	75	
t _r	Turn-off fall time	$V_s = 0V$		25	40	
t _{DM}	Delay matching				50	ns
t _{DT}	Deadtime		200	315	430	ns
t _{DTM}	Deadtime matching				50	ns

Timing Waveforms



 $t_{DM} = |t_{ON} - t_{OFF}|$

Figure 1. Switching Time Waveform Definitions

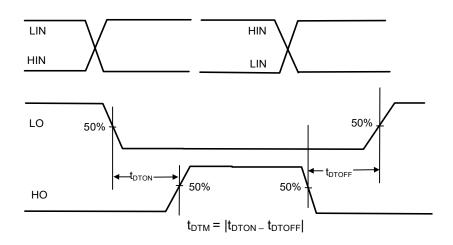
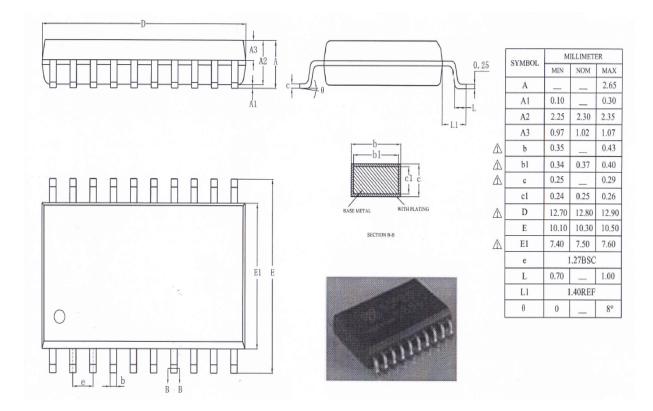


Figure 2. Deadtime Waveform Definitions







Rev.	Change	Owner	Date
1.0	First release, advanced information datasheet	Duke Walton	10/20/2022

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